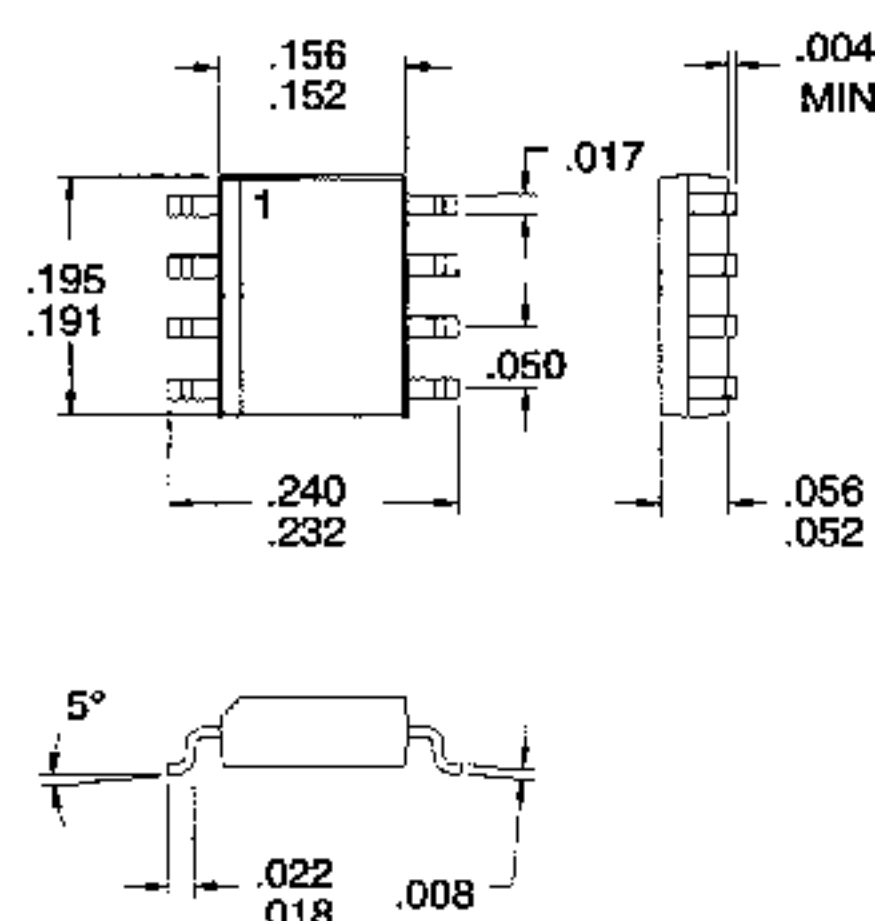


Typical Applications

- General Purpose High Bandwidth Gain Blocks
- IF or RF Buffer Amplifiers
- Broadband Test Equipment
- Final PA for Medium Power Applications
- Driver Stage for Power Amplifiers

Product Description

The RF2311 is a general purpose, low cost low power RF amplifier IC. The device is manufactured on an advanced Gallium Arsenide Heterojunction Bipolar Transistor (HBT) process, and has been designed for use as an easily cascadable 50Ω gain block. Applications include IF and RF amplification in wireless voice and data communication products operating in frequency bands up to 1600MHz. The gain flatness and high bandwidth make the device suitable for many other applications as well. The device is self-contained with 50Ω input and output impedances, and no external DC biasing elements are required to operate as specified.



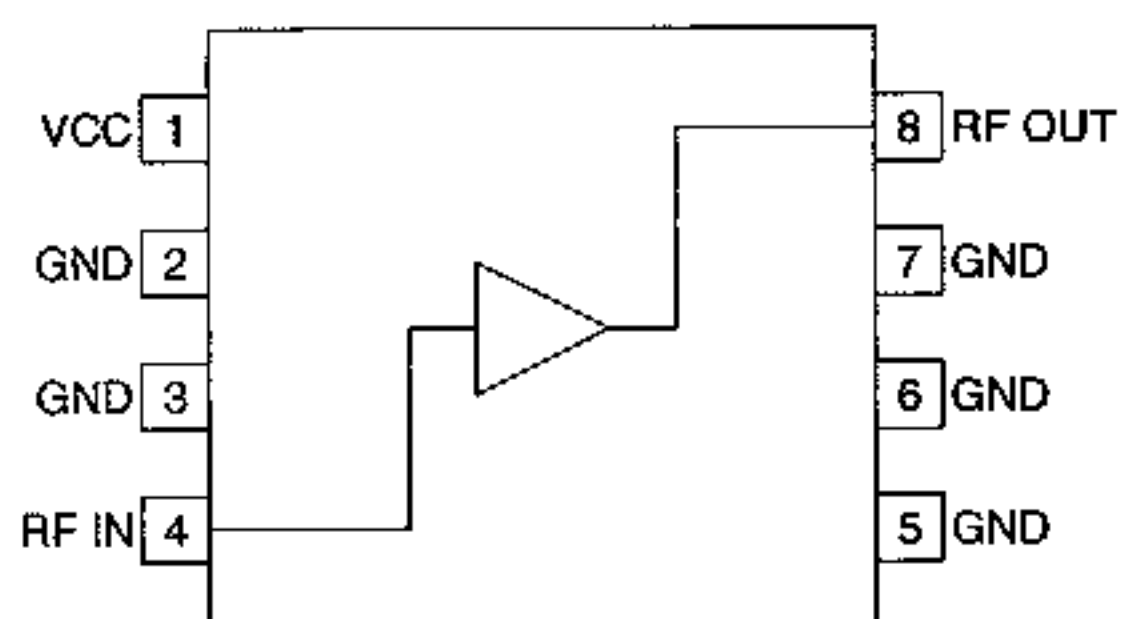
Optimum Technology Matching® Applied

- | | | |
|-------------------------------------|--|--------------------------------------|
| ☐ Si BJT | ☒ GaAs HBT | ☐ GaAs MESFET |
| ☐ Si Bi-CMOS | ☐ SiGe HBT | ☐ Si CMOS |

Package Style: SOP-8

Features

- DC to well over 1600MHz Operation
- Internally Matched Input and Output
- 14dB Small Signal Gain
- 4.2dB Noise Figure
- +9dBm Output Power
- Single 2.7V to 6V Positive Power Supply



Functional Block Diagram

Ordering Information

- | | |
|-------------|----------------------------------|
| RF2311 | General Purpose Amplifier |
| RF2311 PCBA | Fully Assembled Evaluation Board |

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